# DIODES

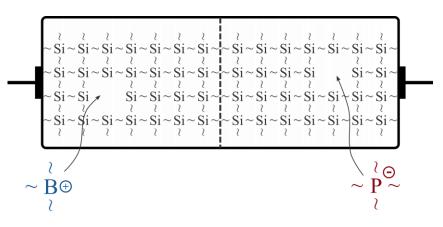
- What is a p-n junction?
- How p-n junction/diode operates?
- How do we address and use diodes in circuits?
- Types of diodes.

Diodes - p-n junction

How is the p-n junction created?

Silicon wafer (substrate, slice)

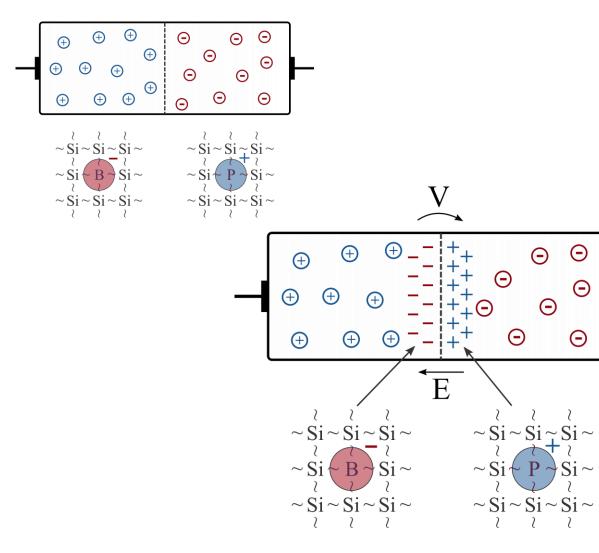
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,	$\sim {\stackrel{\scriptstyle \scriptstyle \sim}{\rm Si}}\sim {\stackrel{\scriptstyle \scriptstyle \scriptstyle \sim}{\rm S}}$	≀ i∼Si∼	$\frac{2}{Si} \sim S$	≀ i∼Si∼	2 ~Si~	2 ~Si~	≥ Si~	≀ Si~	≥ Si~	≥ Si~	≀ Si~	≀ Si~
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ľ	$\sim \operatorname{Si}_{2} \sim \operatorname{Si}_{2}$	$1 \sim S_1 \sim \frac{1}{2}$	$2$ S1 $\sim$ S 2 $2$	$1 \sim S_1 \sim \frac{1}{2}$	$\sim S_1 \sim \frac{1}{2}$	$\sim S_1 \sim \frac{1}{2}$	$\frac{S_1}{2}$	$S_1 \sim 2$	$\frac{S_1}{2}$	$S_1 \sim 2$	$\frac{S_1}{2}$	$\frac{S1}{2}$
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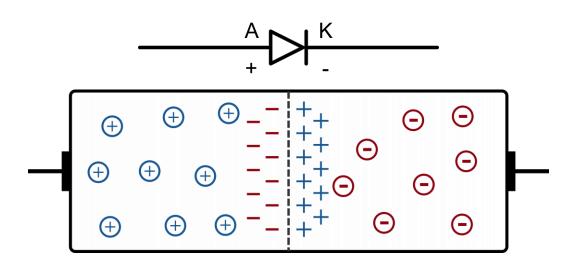


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Diodes - p-n junction

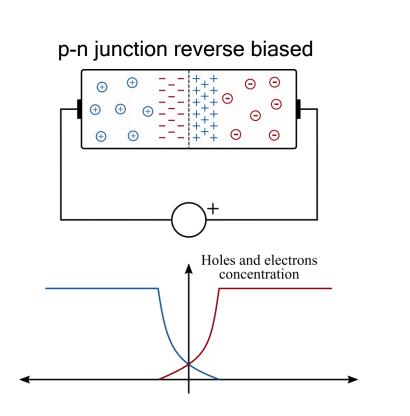
#### How is the p-n junction created?





P-type junction *p*<sup>+</sup> majority charge *e*<sup>-</sup> minority charge N-type junction  $p^+$  minority charge *e* majority charge

Diodes - p-n junction polarization



p-n junction forward biased Θ Ð Θ (+)Θ (+)Θ Θ Ð  $\oplus$ Θ Ð Ð ΘΘ  $\oplus$ Θ Holes and electrons concentration Θ Ð Θ Ð Θ E Θ 0 Ð Θ  $\oplus$ Θ Θ

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$$p_c = p_{c0} \left( e^{kT\nu_d/q_e} - 1 \right)$$
$$\frac{dq(t)}{dt} = i(t) - \frac{q(t)}{\tau_L}$$
$$i(t) = \frac{q(t)}{\tau_L} = \frac{Q}{\tau_L} \left( e^{kT\nu_d(t)/q_e} - 1 \right)$$
$$= I_0 \left( e^{kT\nu_d(t)/q_e} - 1 \right)$$

k - Boltzmann's constant

T - temperature

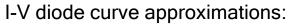
 $q_e$  - the charge of the electron

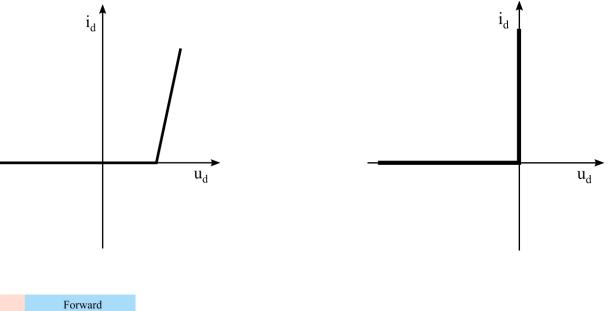
 $\tau_L$  - minority carriers (recombination) lifetime

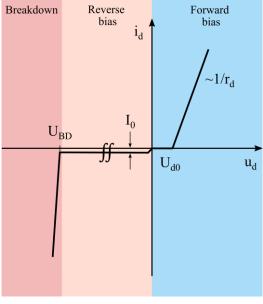
Diodes - I-V curve (static)

 $i_d$  $-1/r_d$  $U_{BD}$  $\int \int \int U_{d0}$   $u_d$ 

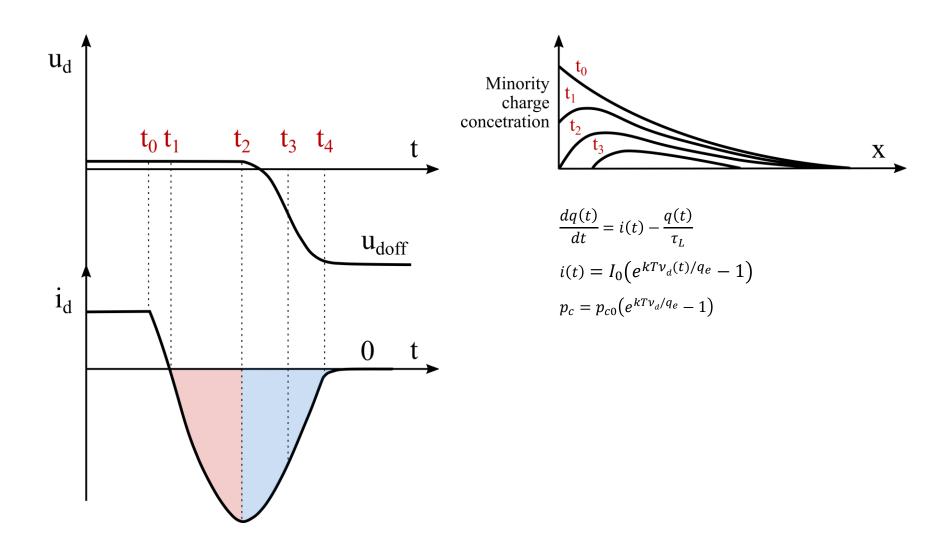
 $\begin{array}{l} u_{d} - \text{diode voltage} \\ i_{d} - \text{diode current} \\ U_{d0} - \text{diode turn-on voltage} \\ r_{d} - \text{diode internal resistance} \\ I_{0} - \text{diode leakage current} \\ U_{BD} - \text{diode breakdown voltage} \end{array}$ 







#### Diodes - Reverse recovery process

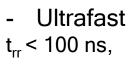


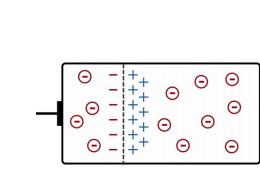
Diodes - types

Power diodes:



- Rectifying diodes  $t_{rr} = n \cdot \mu s$
- Fast t<sub>rr</sub> < μs, t<sub>rr</sub> > 100 ns,





Light-emitting diodes



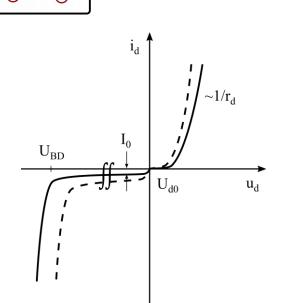


Zener diodes

Photodiodes



- Schottky Unipolar (majority carrier) device Small(er)  $U_{do}$  (0.3 - 0.6 V), More efficient, Negligible reverse recovery process, Smaller  $U_{BD}$ , Higher  $I_0$ .



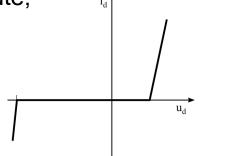
Diodes - packages



Diodes - important notes

Diodes are:

- Uncontrollable semiconductor devices,
- Turned ON and OFF by the circuit in which they are placed,
- Turned ON when the circuit imposes the "higher-thanzero" u<sub>d</sub> *voltage*,
- Turned OFF when the circuit forces the diode *current* to fall to "zero",
- The first approximation is used for diode losses estimation in the ON state,  $i_a^{\dagger}$



1<sub>d</sub>

 $\mathbf{u}_{\mathrm{d}}$ 

Diodes have complicated turn OFF process (reverse recovery process).